



## Description

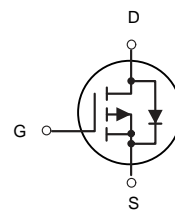
The IPD042P03L3G uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



## General Features

$V_{DS} = -30V$   $I_D = -120A$

$R_{DS(ON)} < 4.5m\Omega @ V_{GS} = -10V$



P-Channel MOSFET

## Application

Lithium battery protection

Wireless impact

Mobile phone fast charging

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IPD042P03L3G	TO-252-2L	HXY MOSFET	2500

## Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Max.	Units
VDSS	Drain-Source Voltage	-30	V
VGSS	Gate-Source Voltage	±20	V
ID	Continuous Drain Current $T_C = 25^\circ C$	-120	A
ID	Continuous Drain Current $T_C = 100^\circ C$	-80	A
IDM	Pulsed Drain Current <sup>note1</sup>	-470	A
EAS	Single Pulsed Avalanche Energy <sup>note2</sup>	580	mJ
PD	Power Dissipation $T_C = 25^\circ C$	100	W
RθJC	Thermal Resistance, Junction to Case	1.4	°C/W
TJ, TSTG	Operating and Storage Temperature Range	-55 to +175	°C



**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$  unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=-250\mu A$	-30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-30V$ , $V_{GS}=0V$			-1	$\mu A$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=-250\mu A$	-1	-1.7	-2.5	V
$g_{FS}$	Forward Transconductance	$V_{DS}=-5V$ , $I_D=-20A$		65		S
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS}=-10V$ , $I_D=-20A$		3.7	4.5	m $\Omega$
		$V_{GS}=-4.5V$ , $I_D=-20A$		6	8.2	m $\Omega$
$C_{iss}$	Input Capacitance	$V_{DS}=-15V$ , $V_{GS}=0V$ , $f=1.0MHz$		7000		pF
$C_{oss}$	Output Capacitance			820		pF
$C_{rss}$	Reverse Transfer Capacitance			540		pF
$R_g$	Gate resistance	$V_{GS}=0V$ , $V_{DS}=0V$ , $f=1.0MHz$		2.2		$\Omega$
$t_{d(on)}$	Turn-on Delay Time	$V_{GS}=-10V$ , $V_{DS}=-15V$ , $R_L=0.75\Omega$ , $R_{GEN}=3\Omega$		14		nS
$t_r$	Turn-on Rise Time			13		nS
$t_{d(off)}$	Turn-Off Delay Time			65		nS
$t_f$	Turn-Off Fall Time			37		nS
$Q_g$	Total Gate Charge	$V_{GS}=-10V$ , $V_{DS}=-15V$ , $I_D=-20A$		130		nC
$Q_{gs}$	Gate-Source Charge			12		nC
$Q_{gd}$	Gate-Drain Charge			31		nC
$I_{SD}$	Source-Drain Current (Body Diode)				-108	A
$V_{SD}$	Forward on Voltage (Note 3)	$V_{GS}=0V$ , $I_S=-20A$			-1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=-20A$ , $di/dt=100A/\mu s$		30		ns
$Q_{rr}$	Reverse Recovery Charge	$I_F=-20A$ , $di/dt=100A/\mu s$		40		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

Notes 2. $E_{AS}$  condition:  $T_J=25^{\circ}\text{C}$ ,  $V_{DD}=15V$ ,  $V_G=-10V$ ,  $R_g=25\Omega$ ,  $L=0.5mH$ .

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



## Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

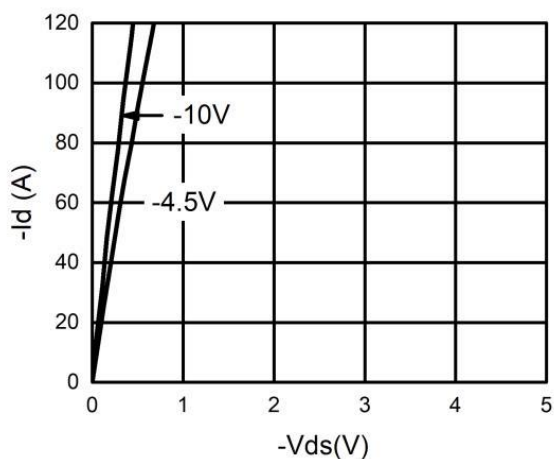


Figure 2. Transfer Characteristics

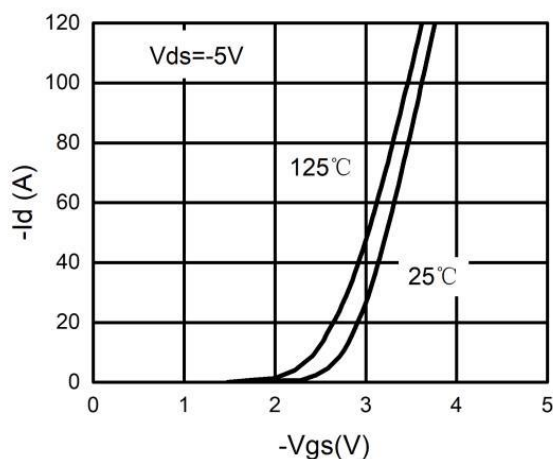


Figure 3. Power Dissipation

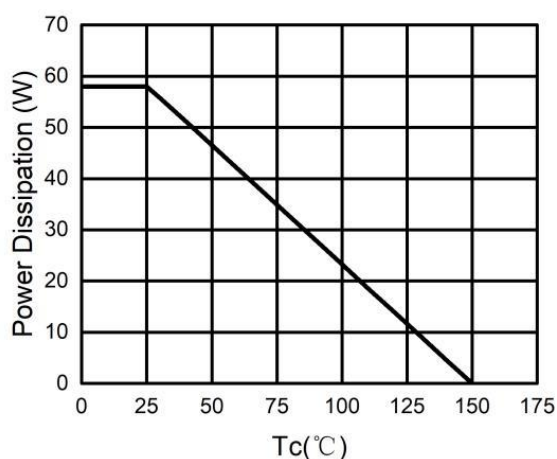


Figure 4. Drain Current

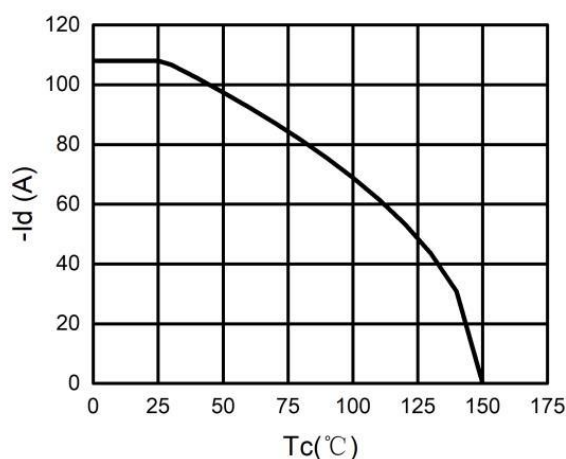


Figure 5.  $BV_{DSS}$  vs Junction Temperature

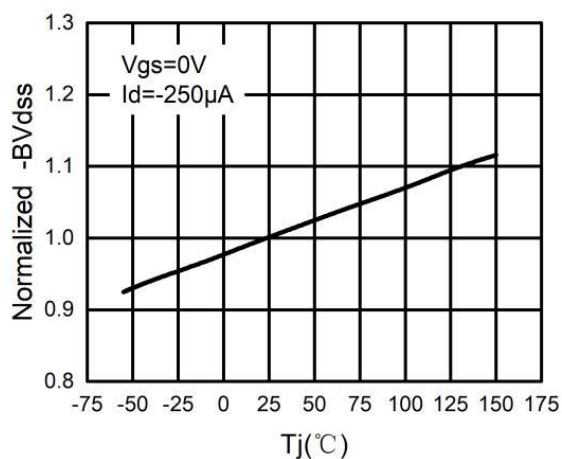


Figure 6.  $R_{DS(ON)}$  vs Junction Temperature

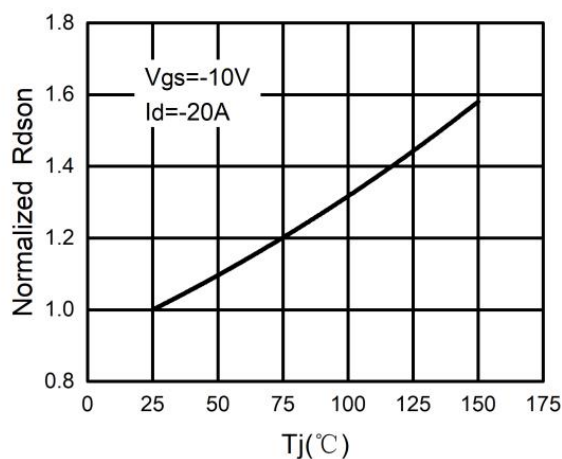




Figure 7. Gate Charge Waveforms

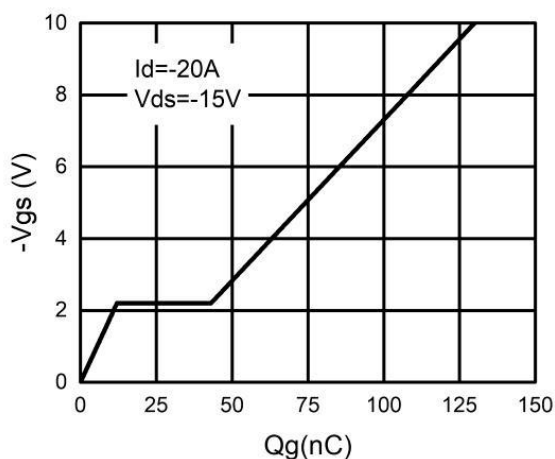


Figure 8. Capacitance

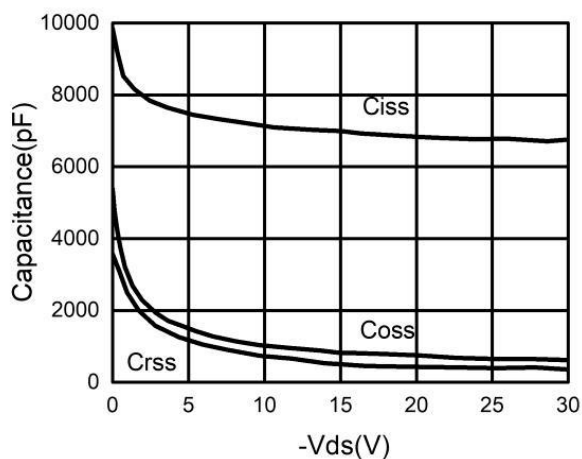


Figure 9. Body-Diode Characteristics

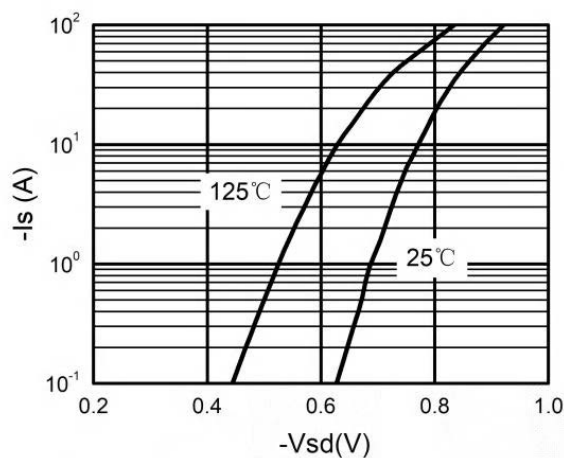
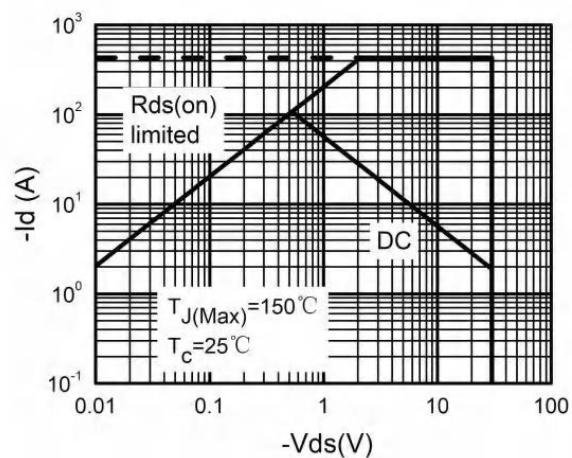
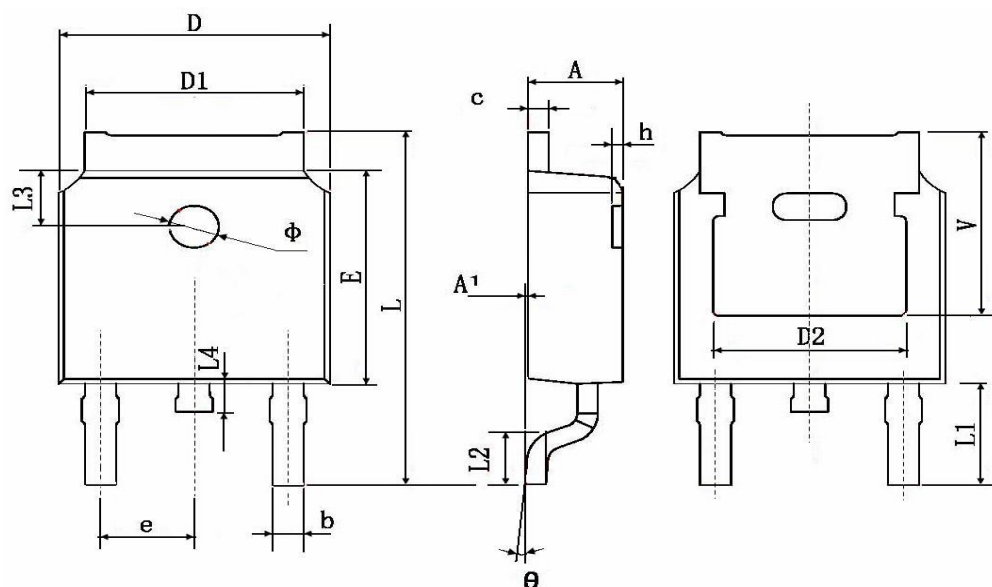


Figure 10. Maximum Safe Operating Area





## TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



### **Attention**

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.